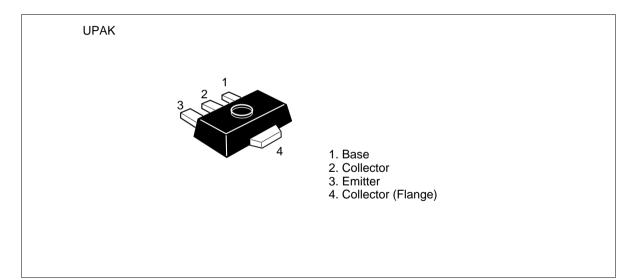
Silicon PNP Epitaxial

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Application

- Low frequency power amplifier
- Complementary pair with 2SD1368

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit	
Collector to base voltage	V _{CBO}	-70	V	
Collector to emitter voltage	V _{CEO}	-50	V	
Emitter to base voltage	V _{EBO}	-6	V	
Collector current	Ι _c	-1	А	
Collector peak current	i _{C(peak)} *1	-1.5	А	
Collector power dissipation	Pc*2	1	W	-
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. $PW \le 10 \text{ ms}$, Duty cycle $\le 20\%$

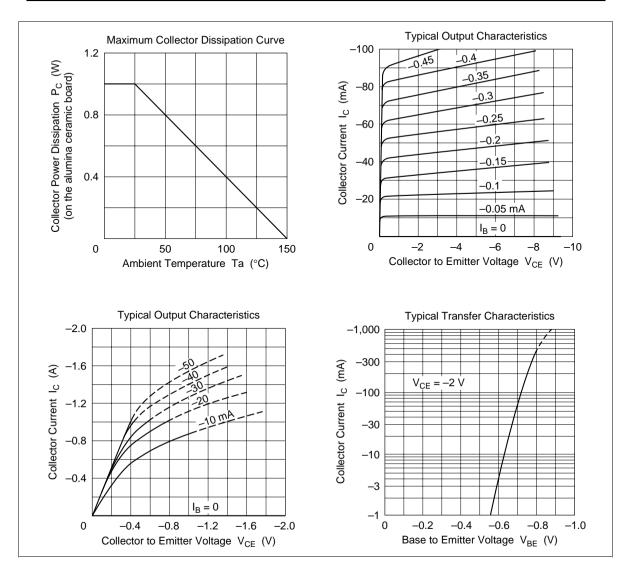
2. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

Electrical Characteristics (Ta = 25°C)

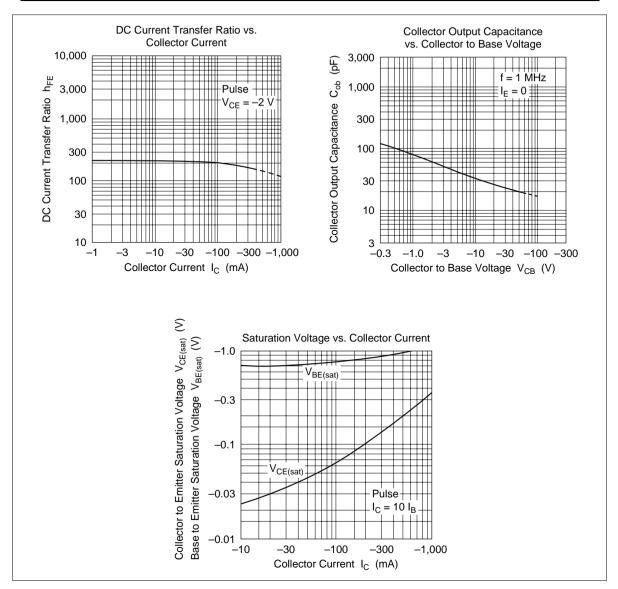
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	-70	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	-50	_	_	V	$I_c = -1 \text{ mA}, \text{ R}_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	_	_	V	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	-0.1	μΑ	$V_{CB} = -50 \text{ V}, \text{ I}_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	-0.1	μΑ	$V_{EB} = -4 V, I_{C} = 0$
DC current transfer ratio	$h_{\rm FE}^{*1}$	100	_	320		$V_{ce} = -2 \text{ V}, \text{ I}_{c} = -0.1 \text{ A}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	—	-0.6	V	$I_c = -1 A,$ $I_B = -0.1 A (Pulse test)$
Base to emitter saturation voltage	$V_{\text{BE(sat)}}$	—	—	-1.2	V	$I_c = -1 A,$ $I_B = -0.1 A (Pulse test)$
Gain bandwidth product	f _T	—	150	—	MHz	$V_{ce} = -2 V,$ $I_c = -10 mA (Pulse test)$
Collector output capacitance	Cob	—	35	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0,$ f = 1 MHz
Note: 1. The 2SB1002 is grouped by h _{FE} as follows.						
Mark CH CJ						

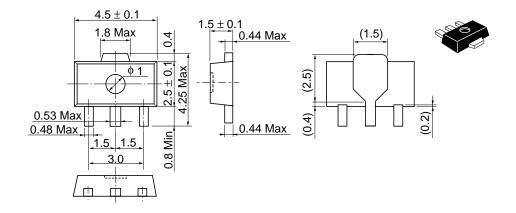
h_{FE} 100 to 200 160 to 320

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Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g

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